

Amendments to the Claims:

Please amend the claims as follows:

Claims 1-14 (Canceled).

Claim 15 (Original): A method for fabricating a semiconductor integrated circuit device comprising a substrate, and a spiral inductor which is formed on the substrate and which includes a spiral conductive layer serving as an induction element, said method comprising:

forming an element isolating groove in the surface of the substrate so that a protruding portion is formed in a region other than the region in which said conductive layer is formed, the top of said protruding portion serving as a dummy element for controlling a chemical mechanical polishing process.

Claim 16 (Currently Amended): A method for fabricating a semiconductor integrated circuit device ~~as set forth in claim~~ as set forth in claim 15, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

Claim 17 (Original): A method for fabricating a semiconductor integrated circuit device comprising a substrate, and a spiral inductor which is formed on the substrate so as to have a spiral shape and which includes a conductive layer serving as an induction element, said method comprising:

forming an element isolating groove in the surface of the substrate so that a protruding portion is formed, the top thereof serving as a dummy element for controlling a chemical mechanical polishing process;

depositing a protective film on the substrate;

selectively removing said protective film in a region other than a region in which said induction element is to be formed, by patterning using a photoresist; and

silicidating the surface of the substrate.

Claim 18 (Original): A method for fabricating a semiconductor integrated circuit device as set forth in claim 17, wherein the substrate is an SOI substrate, and said protruding portion is formed of an SOI layer of said SOI substrate.

Claim 19 (Original): A method for fabricating a semiconductor integrated circuit device as set forth in claim 17, wherein said protruding portion is formed in a region other than a region directly below said conductive layer.

Claim 20 (Currently Amended): A method for fabricating a semiconductor integrated circuit ~~as set forth in claim~~ as set forth in claim 19, wherein the substrate is an SOI substrate, and said protruding portion is formed of an SOI layer of said SOI substrate.